

# W Walukiewicz

## List of Publications by Year in descending order

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257  
papers

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257  
docs citations

257  
times ranked

8945  
citing authors

#	ARTICLE	IF	CITATIONS
1	Conduction band modifications by d states in vanadium doped CdO. Journal of Alloys and Compounds, 2020, 822, 153567.	2.8	6
2	Photoreflectance and photoinduced microwave reflectance studies of surface band bending in Mg-doped InN. Journal of Applied Physics, 2019, 126, 045712.	1.1	3
3	Growth of GaP <sub>1-x</sub> As <sub>x</sub> on Si substrates by chemical beam epitaxy. Journal of Applied Physics, 2019, 126, 105704.	1.1	4
4	Effects of the host conduction band energy on the electronic band structure of ZnCdTeO dilute oxide alloys. Journal of Applied Physics, 2019, 126, 083106.	1.1	5
5	ZnO <sub>1-x</sub> Te <sub>x</sub> highly mismatched alloys beyond the dilute alloy limit: Synthesis and electronic band structure. Journal of Applied Physics, 2019, 125, 155702.	1.1	13
6	THz transient photoconductivity of the III-V dilute nitride GaP <sub>1-x</sub> As <sub>x</sub> N <sub>y</sub> . Semiconductor Science and Technology, 2018, 33, 125009.	1.0	3
7	Photoreflectance studies of optical transitions in GaNPAs intermediate band solar cell absorbers. Solar Energy Materials and Solar Cells, 2018, 188, 99-104.	3.0	6
8	Carrier Lifetimes in a GaN <sub>1-x</sub> N <sub>y</sub> Intermediate-Band Semiconductor. Physical Review Applied, 2017, 7, .	1.5	10
9	Multicolor emission from intermediate band semiconductor ZnO <sub>1-x</sub> Se <sub>x</sub> . Scientific Reports, 2017, 7, 44214.	1.6	19
10	Effects of band anticrossing on the temperature dependence of the band gap of ZnSe <sub>1-x</sub> O <sub>x</sub> alloys. Semiconductor Science and Technology, 2017, 32, 015005.	1.0	5
11	Nitrogen-related intermediate band in P-rich GaN <sub>1-x</sub> PyAs <sub>1-x</sub> y alloys. Scientific Reports, 2017, 7, 15703.	1.6	16
12	Undoped GaN <sub>1-x</sub> Sb <sub>x</sub> alloys: Effects of annealing. Applied Physics Letters, 2016, 109, .	1.5	6
13	Highly mismatched GaN <sub>1-x</sub> Sb <sub>x</sub> alloys: synthesis, structure and electronic properties. Semiconductor Science and Technology, 2016, 31, 083001.	1.0	16
14	Growth and characterization of highly mismatched Zn <sub>1-x</sub> CdxTe <sub>1-y</sub> O <sub>y</sub> alloys for intermediate band solar cells. , 2015, , .		1
15	Evidence of extreme type-III band offset at buried GaN <sub>1-x</sub> CdO/SnTe interfaces. Physical Review B, 2015, 91, .	1.1	7
16	Growth and characterization of ZnO <sub>1-x</sub> S <sub>x</sub> highly mismatched alloys over the entire composition. Journal of Applied Physics, 2015, 118, .	1.1	43
17	Electronic band structure of highly mismatched GaN <sub>1-x</sub> Sbx alloys in a broad composition range. Applied Physics Letters, 2015, 107, .	1.5	25
18	Fabrication and characterization of multiband solar cells based on highly mismatched alloys. Journal of Physics: Conference Series, 2015, 647, 012067.	0.3	0

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19	Electronic band structure of ZnO-rich highly mismatched ZnO $_{1-x}$ Te $_x$ alloys. Applied Physics Letters, 2015, 106, .	1.5	27
20	Effects of a semiconductor matrix on the band anticrossing in dilute group II-VI oxides. Semiconductor Science and Technology, 2015, 30, 085018.	1.0	18
21	InGaN pn-junctions grown by PA-MBE: Material characterization and fabrication of nanocolumn electroluminescent devices. Journal of Crystal Growth, 2015, 425, 393-397.	0.7	8
22	Effects of native defects on properties of low temperature grown, non-stoichiometric gallium nitride. Journal Physics D: Applied Physics, 2015, 48, 385101.	1.3	6
23	Temperature evolution of carrier dynamics in GaN $_x$ PyAs $_{1-y}$ alloys. Journal of Applied Physics, 2015, 117, .	1.1	18
24	Effects of the d-donor level of vanadium on the properties of Zn $_{1-x}$ V $_x$ O films. Applied Physics Letters, 2015, 106, .	1.5	12
25	Surface photovoltage and modulation spectroscopy of E $_{\text{a}}$ and E $_{\text{+}}$ transitions in GaNAs layers. Thin Solid Films, 2014, 567, 101-104.	0.8	17
26	Composition and optical properties of dilute-Sb GaN $_{1-x}$ Sb $_x$ highly mismatched alloys grown by MBE. Journal Physics D: Applied Physics, 2014, 47, 465102.	1.3	9
27	Modeling of the atomic structure and electronic properties of amorphous GaN $_{1-x}$ As $_x$ . Computational Materials Science, 2014, 82, 100-106.	1.4	15
28	Growth and characterization of highly mismatched GaN $_{1-x}$ Sb $_x$ alloys. Journal of Applied Physics, 2014, 116, .	1.1	20
29	Electronic Band Structure of $\text{GaN}_{1-x}\text{Sb}_x$ alloys. Physical Review Applied, 2014, 1, .	1.9	71
30	GaNAsP: An intermediate band semiconductor grown by gas-source molecular beam epitaxy. Applied Physics Letters, 2013, 102, .	1.5	37
31	Crystal structure and properties of Cd $_x$ Zn $_{1-x}$ O alloys across the full composition range. Applied Physics Letters, 2013, 102, .	1.5	60
32	Highly mismatched N-rich GaN $_{1-x}$ Sb $_x$ films grown by low temperature molecular beam epitaxy. Applied Physics Letters, 2013, 102, .	1.5	26
33	Local structure of amorphous GaN $_{1-x}$ As $_x$ semiconductor alloys across the composition range. Journal of Applied Physics, 2013, 113, .	1.1	6
34	P-type InGaN across the entire alloy composition range. Applied Physics Letters, 2013, 102, 102111.	1.5	13
35	Temperature dependence of photoluminescence from InNAsSb layers: The role of localized and free carrier emission in determination of temperature dependence of energy gap. Applied Physics Letters, 2013, 102, .	1.5	21
36	Temperature dependence of E and E $_{\text{+}}$ SO transitions in In $_{0.53}$ Ga $_{0.47}$ Bi $_x$ As $_{1-x}$ alloys studied by photoreflectance. Journal of Applied Physics, 2012, 112, .	1.1	14

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37	Synthesis and optical properties of ZnTe <sub>1-x</sub> O <sub>x</sub> highly mismatched alloys for intermediate band solar cells. , 2012, , .		0
38	Correlations between the band structure, activation energies of electron traps, and photoluminescence in n-type GaNAs layers. Applied Physics Letters, 2012, 101, 082109.	1.5	19
39	Controlling the Curie temperature in (Ga,Mn)As through location of the Fermi level within the impurity band. Nature Materials, 2012, 11, 444-449.	13.3	168
40	Engineering the Electronic Band Structure for Multiband Solar Cells. Physical Review Letters, 2011, 106, 028701.	2.9	282
41	Thermal stability of amorphous GaN <sub>1-x</sub> As <sub>x</sub> alloys. Applied Physics Letters, 2011, 98, 161902.	1.5	8
42	Electronic structure of CdO studied by soft X-ray spectroscopy. Journal of Electron Spectroscopy and Related Phenomena, 2011, 184, 249-253.	0.8	25
43	Mg doped InN and confirmation of free holes in InN. Applied Physics Letters, 2011, 98, 042104.	1.5	44
44	Doping of GaN <sub>1-x</sub> As <sub>x</sub> with high As content. Journal of Applied Physics, 2011, 110, 093702.	1.1	4
45	Intermediate band solar cell: Proof of concept. , 2011, , .		0
46	Effects of point defects on thermal and thermoelectric properties of InN. Applied Physics Letters, 2011, 98, .	1.5	42
47	Finite element simulations of compositionally graded InGaN solar cells. Solar Energy Materials and Solar Cells, 2010, 94, 478-483.	3.0	192
48	High quality In <sub>x</sub> Ga <sub>1-x</sub> N thin films with x ≈ 0.2 grown on silicon. Physica Status Solidi (B): Basic Research, 2010, 247, 1747-1749.	0.7	15
49	Amorphous GaN <sub>1-x</sub> As <sub>x</sub> alloys for multi-junction solar cells. , 2010, , .		0
50	GaN <sub>1-x</sub> Bi <sub>x</sub> : Extremely mismatched semiconductor alloys. Applied Physics Letters, 2010, 97, 141919.	1.5	33
51	Fermi level stabilization energy in cadmium oxide. Journal of Applied Physics, 2010, 107, .	1.1	66
52	Full multiple scattering analysis of XANES at the Cd <sub>1-x</sub> O <sub>x</sub> interface in CdO films combined with a soft-x-ray emission investigation. Physical Review B, 2010, 82, .	1.1	36
53	Electronic structure of Ga <sub>1-x</sub> N <sub>x</sub> according to hole-concentration-dependent measurements. Physical Review B, 2010, 81, .	1.1	16
54	Hole transport and photoluminescence in Mg-doped InN. Journal of Applied Physics, 2010, 107, .	1.1	67

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55	Low gap amorphous GaN $_{1-x}$ As $_x$ alloys grown on glass substrate. Applied Physics Letters, 2010, 97, .	1.5	18
56	Highly mismatched crystalline and amorphous GaN $_{1-x}$ As $_x$ alloys in the whole composition range. Journal of Applied Physics, 2009, 106, .	1.1	61
57	Numerical simulations of novel InGaN solar cells. , 2009, , .		4
58	MBE GROWTH AND CHARACTERIZATION OF Mg-DOPED III-NITRIDES ON SAPPHIRE. Selected Topics in Electronics and Systems, 2009, , 113-119.	0.2	0
59	Properties of native point defects in In $_{1-x}$ Al $_x$ N alloys. Journal Physics D: Applied Physics, 2009, 42, 095406.	1.3	3
60	Determining surface Fermi level pinning position of InN nanowires using electrolyte gating. Applied Physics Letters, 2009, 95, .	1.5	16
61	MBE GROWTH AND CHARACTERIZATION OF Mg-DOPED III-NITRIDES ON SAPPHIRE. International Journal of High Speed Electronics and Systems, 2009, 19, 113-119.	0.3	0
62	Electrical and electrothermal transport in InN: The roles of defects. Physica B: Condensed Matter, 2009, 404, 4862-4865.	1.3	11
63	Temperature dependence of the band gap of ZnSe $_{1-x}$ O $_x$ . Applied Physics Letters, 2009, 95, 151907.	1.5	34
64	Electronic Properties of InN and InGaN. , 2009, , 377-417.		0
65	Low-temperature grown compositionally graded InGaN films. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1866-1869.	0.8	17
66	Mg-doped InN and InGaN Photoluminescence, capacitance-voltage and thermopower measurements. Physica Status Solidi (B): Basic Research, 2008, 245, 873-877.	0.7	55
67	Chapter 3 Fermi Level Effects on Mn Incorporation in III-Mn-V Ferromagnetic Semiconductors. Semiconductors and Semimetals, 2008, 82, 89-133.	0.4	3
68	Electronic Band Structure of Highly Mismatched Semiconductor Alloys. , 2008, , 65-89.		5
69	Formation of Mn-derived impurity band in III-Mn-V alloys by valence band anticrossing. Physical Review B, 2008, 78, .	1.1	50
70	Modeling of InGaN/Si tandem solar cells. Journal of Applied Physics, 2008, 104, .	1.1	139
71	Band gap bowing parameter of In $_{1-x}$ Al $_x$ N. Journal of Applied Physics, 2008, 104, .	1.1	67
72	Composition dependence of the hole mobility in GaSb $_x$ As $_{1-x}$ . Applied Physics Letters, 2008, 92, 162105.	1.5	4

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73	Probing and modulating surface electron accumulation in InN by the electrolyte gated Hall effect. Applied Physics Letters, 2008, 93, .	1.5	31
74	Properties of Ga <sub>1-x</sub> MnxAs with high $\epsilon$ (>0.1). Journal of Applied Physics, 2008, 103, .	1.1	20
75	Effects of donor doping on Ga <sub>1-x</sub> MnxAs. Applied Physics Letters, 2008, 93, .	1.5	19
76	Band anticrossing in highly mismatched $\text{Sn}_x\text{Ge}_{1-x}\text{Mn}_y\text{As}$ alloys. Physical Review B, 2008, 77, .	1.1	66
77	Optimum nitride concentration in multiband III-N $\epsilon$ V alloys for high efficiency ideal solar cells. Applied Physics Letters, 2008, 93, 174109.	1.5	18
78	Characterization of MG-doped InGaN and InAlN alloys grown by MBE for solar applications. Conference Record of the IEEE Photovoltaic Specialists Conference, 2008, , .	0.0	4
79	Metal-Insulator Transition by Isovalent Anion Substitution in Ga <sub>1-x</sub> MnxAs: Implications to Ferromagnetism. Physical Review Letters, 2008, 101, 087203.	2.9	34
80	Energetic Beam Synthesis of Dilute Nitrides and Related Alloys. , 2008, , 1-34.		0
81	Towards identification of localized donor states in InN. Semiconductor Science and Technology, 2007, 22, 1161-1164.	1.0	3
82	High electron mobility InN. Applied Physics Letters, 2007, 90, 162103.	1.5	29
83	Compensating point defects in He <sup>+</sup> -irradiated InN. Physical Review B, 2007, 75, .	1.1	42
84	Electron mobility in InN and III-N alloys. Journal of Applied Physics, 2007, 102, 073705.	1.1	52
85	Valence-band anticrossing in mismatched III-V semiconductor alloys. Physical Review B, 2007, 75, .	1.1	354
86	Effects of surface states on electrical characteristics of InN and In <sub>1-x</sub> GaxN. Physical Review B, 2007, 76, .	1.1	61
87	Effects of Quantum Confinement on the Doping Limit of Semiconductor Nanowires. Nano Letters, 2007, 7, 1186-1190.	4.5	67
88	TEM studies of as-grown, irradiated and annealed InN films. Physica B: Condensed Matter, 2007, 401-402, 646-649.	1.3	8
89	p-type InN and In-rich InGaN. Physica Status Solidi (B): Basic Research, 2007, 244, 1820-1824.	0.7	23
90	Synthesis of highly mismatched alloys using ion implantation and pulsed laser melting. Nuclear Instruments & Methods in Physics Research B, 2007, 261, 1150-1154.	0.6	9

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91	Optical bleaching effect in InN epitaxial layers. Applied Physics Letters, 2006, 88, 191109.	1.5	22
92	Structure and electronic properties of InN and In-rich group III-nitride alloys. Journal Physics D: Applied Physics, 2006, 39, R83-R99.	1.3	229
93	Evidence for p-Type Doping of InN. Physical Review Letters, 2006, 96, 125505.	2.9	193
94	Multiband GaNAsP quaternary alloys. Applied Physics Letters, 2006, 88, 092110.	1.5	128
95	Dopants and defects in InN and InGaN alloys. Journal of Crystal Growth, 2006, 288, 278-282.	0.7	13
96	Native defects in In <sub>x</sub> Ga <sub>1-x</sub> N alloys. Physica B: Condensed Matter, 2006, 376-377, 432-435.	1.3	8
97	Native-defect-controlled n-type conductivity in InN. Physica B: Condensed Matter, 2006, 376-377, 436-439.	1.3	24
98	Defects and Self-Compensation in Semiconductors. Springer Series in Materials Science, 2006, , 35-54.	0.4	6
99	Photoluminescence of energetic particle-irradiated In <sub>x</sub> Ga <sub>1-x</sub> N alloys. Applied Physics Letters, 2006, 88, 151101.	1.5	12
100	Electron Transport Properties of InN. Materials Research Society Symposia Proceedings, 2005, 892, 91.	0.1	5
101	Effect of native defects on optical properties of In <sub>x</sub> Ga <sub>1-x</sub> N alloys. Applied Physics Letters, 2005, 87, 161905.	1.5	18
102	On the crystalline structure, stoichiometry and band gap of InN thin films. Applied Physics Letters, 2005, 86, 071910.	1.5	103
103	Multiphonon resonance Raman scattering in In <sub>x</sub> Ga <sub>1-x</sub> N. Physical Review B, 2005, 72, .	1.1	21
104	Group III-nitride Materials for High Efficiency Photoelectrochemical Cells. Materials Research Society Symposia Proceedings, 2005, 884, 1.	0.1	3
105	Electronic and Optical Properties of Energetic Particle-Irradiated In-rich InGaN. Materials Research Society Symposia Proceedings, 2005, 864, 7101.	0.1	1
106	Highly Mismatched Alloys for Intermediate Band Solar Cells. Materials Research Society Symposia Proceedings, 2005, 865, 571.	0.1	8
107	Mutual Passivation in Dilute GaN <sub>x</sub> As <sub>1-x</sub> Alloys. Materials Research Society Symposia Proceedings, 2005, 864, 811.	0.1	0
108	Pressure-dependent photoluminescence study of ZnO nanowires. Applied Physics Letters, 2005, 86, 153117.	1.5	83

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109	Strain-engineered ferromagnetic $\text{In}_{1-x}\text{Mn}_x\text{As}$ films with in-plane easy axis. Applied Physics Letters, 2005, 86, 112512.	1.5	23
110	Fermi-level stabilization energy in group III nitrides. Physical Review B, 2005, 71, .	1.1	190
111	Effect of film thickness on the incorporation of Mn interstitials in $\text{Ga}_{1-x}\text{Mn}_x\text{As}$ . Applied Physics Letters, 2005, 86, 042102.	1.5	29
112	Band Anticrossing and Related Electronic Structure in III-V Alloys. , 2005, , 325-359.		5
113	Fermi level effects on Mn incorporation in modulation-doped ferromagnetic III $_{1-x}$ Mn $_x$ V heterostructures. Journal of Physics Condensed Matter, 2004, 16, S5499-S5508.	0.7	7
114	High quality InN/GaN heterostructures grown by migration enhanced metalorganic chemical vapor deposition. Applied Physics Letters, 2004, 84, 1892-1894.	1.5	59
115	Direct evidence of the Fermi-energy-dependent formation of Mn interstitials in modulation-doped $\text{Ga}_{1-x}\text{Al}_x\text{As}/\text{Ga}_{1-x}\text{Mn}_x\text{As}/\text{Ga}_{1-x}\text{Al}_x\text{As}$ heterostructures. Applied Physics Letters, 2004, 84, 4325-4327.	1.5	17
116	Synthesis and optical properties of II-O-VI highly mismatched alloys. Journal of Applied Physics, 2004, 95, 6232-6238.	1.1	82
117	Effects of pressure on the band structure of highly mismatched $\text{Zn}_{1-x}\text{Mn}_x\text{OxTe}_{1-x}$ alloys. Applied Physics Letters, 2004, 84, 924-926.	1.5	10
118	Effects of electron concentration on the optical absorption edge of InN. Applied Physics Letters, 2004, 84, 2805-2807.	1.5	221
119	Compositional Ordering in $\text{In}_x\text{Ga}_{1-x}\text{N}$ and its influence on optical properties. Materials Research Society Symposia Proceedings, 2004, 831, 126.	0.1	1
120	Lattice location of Mn and fundamental Curie temperature limit in ferromagnetic $\text{Ga}_{1-x}\text{Mn}_x\text{As}$ . Nuclear Instruments & Methods in Physics Research B, 2004, 219-220, 636-641.	0.6	6
121	Synthesis and properties of highly mismatched II-VI alloys. IEE Proceedings: Optoelectronics, 2004, 151, 452-459.	0.8	3
122	Mutual passivation effects in highly mismatched group III-V alloys. IEE Proceedings: Optoelectronics, 2004, 151, 460-464.	0.8	5
123	Diluted ZnMnTe oxide: a multi-band semiconductor for high efficiency solar cells. Physica Status Solidi (B): Basic Research, 2004, 241, 660-663.	0.7	25
124	Oxygen induced band-gap reduction in $\text{ZnOxSe}_{1-x}$ alloys. Physica Status Solidi (B): Basic Research, 2004, 241, 603-606.	0.7	6
125	Effects of hydrostatic pressure on optical properties of InN and In-rich group III-nitride alloys. Physica Status Solidi (B): Basic Research, 2004, 241, 3107-3112.	0.7	5
126	Optical properties and electronic structure of InN and In-rich group III-nitride alloys. Journal of Crystal Growth, 2004, 269, 119-127.	0.7	157



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127	Electronic effects determining the formation of ferromagnetic $\text{III}_{1-x}\text{MnxV}$ alloys during epitaxial growth. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2004, 25, 171-180.	1.3	27
128	Valence band hybridization in N-rich $\text{Ga}_{1-x}\text{As}_x$ alloys. <i>Physical Review B</i> , 2004, 70, .	1.1	86
129	Band anticrossing in dilute nitrides. <i>Journal of Physics Condensed Matter</i> , 2004, 16, S3355-S3372.	0.7	34
130	Diluted II-VI Oxide Semiconductors with Multiple Band Gaps. <i>Physical Review Letters</i> , 2003, 91, 246403.	2.9	268
131	Band gaps of InN and group III nitride alloys. <i>Superlattices and Microstructures</i> , 2003, 34, 63-75.	1.4	159
132	Mutual passivation of group IV donors and isovalent nitrogen in diluted $\text{Ga}_x\text{As}_{1-x}$ alloys. <i>Physica B: Condensed Matter</i> , 2003, 340-342, 389-393.	1.3	4
133	Universal bandgap bowing in group-III nitride alloys. <i>Solid State Communications</i> , 2003, 127, 411-414.	0.9	104
134	Temperature dependence of the fundamental band gap of InN. <i>Journal of Applied Physics</i> , 2003, 94, 4457-4460.	1.1	375
135	Superior radiation resistance of $\text{In}_{1-x}\text{Ga}_x\text{N}$ alloys: Full-solar-spectrum photovoltaic material system. <i>Journal of Applied Physics</i> , 2003, 94, 6477-6482.	1.1	572
136	Band-gap bowing effects in $\text{B}_x\text{Ga}_{1-x}\text{As}$ alloys. <i>Journal of Applied Physics</i> , 2003, 93, 2696-2699.	1.1	38
137	Effect of oxygen on the electronic band structure in $\text{ZnO}_x\text{Se}_{1-x}$ alloys. <i>Applied Physics Letters</i> , 2003, 83, 299-301.	1.5	76
138	Composition dependence of the hydrostatic pressure coefficients of the bandgap of $\text{ZnSe}_{1-x}\text{Te}_x$ alloys. <i>Physical Review B</i> , 2003, 68, .	1.1	16
139	Mutual passivation effects in Si-doped diluted $\text{In}_y\text{Ga}_{1-y}\text{As}_{1-x}\text{N}_x$ alloys. <i>Physical Review B</i> , 2003, 68, .	1.1	15
140	Origin of the large band-gap bowing in highly mismatched semiconductor alloys. <i>Physical Review B</i> , 2003, 67, .	1.1	67
141	Mutual passivation of group IV donors and nitrogen in diluted $\text{Ga}_x\text{As}_{1-x}$ alloys. <i>Applied Physics Letters</i> , 2003, 83, 2844-2846.	1.5	17
142	Pressure Dependence of Optical Transitions in In-rich Group III-Nitride Alloys. <i>Materials Research Society Symposia Proceedings</i> , 2003, 798, 301.	0.1	0
143	Hydrostatic pressure dependence of the fundamental bandgap of InN and In-rich group III nitride alloys. <i>Applied Physics Letters</i> , 2003, 83, 4963-4965.	1.5	65
144	Enhancement of Curie temperature in $\text{Ga}_{1-x}\text{MnxAs}/\text{Ga}_{1-y}\text{AlyAs}$ ferromagnetic heterostructures by Be modulation doping. <i>Applied Physics Letters</i> , 2003, 83, 4220-4222.	1.5	70

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145	Synthesis of GaN <sub>x</sub> As <sub>1-x</sub> thin films by pulsed laser melting and rapid thermal annealing of N <sup>+</sup> -implanted GaAs. Journal of Applied Physics, 2003, 94, 1043-1049.	1.1	48
146	Curie temperature limit in ferromagnetic Ga <sub>1-x</sub> Mn <sub>x</sub> As. Physical Review B, 2003, 68, .	1.1	91
147	Determination of free hole concentration in ferromagnetic Ga <sub>1-x</sub> Mn <sub>x</sub> As using electrochemical capacitance-voltage profiling. Applied Physics Letters, 2002, 81, 844-846.	1.5	48
148	Band anticrossing in highly mismatched III-V semiconductor alloys. Semiconductor Science and Technology, 2002, 17, 860-869.	1.0	298
149	Current status of research and development of III-N-V semiconductor alloys. Semiconductor Science and Technology, 2002, 17, 741-745.	1.0	61
150	Enhanced nitrogen incorporation by pulsed laser annealing of GaN <sub>x</sub> As <sub>1-x</sub> formed by N ion implantation. Applied Physics Letters, 2002, 80, 3958-3960.	1.5	28
151	Effect of the location of Mn sites in ferromagnetic Ga <sub>1-x</sub> Mn <sub>x</sub> As on its Curie temperature. Physical Review B, 2002, 65, .	1.1	491
152	Small band gap bowing in In <sub>1-x</sub> Ga <sub>x</sub> N alloys. Applied Physics Letters, 2002, 80, 4741-4743.	1.5	563
153	Unusual properties of the fundamental band gap of InN. Applied Physics Letters, 2002, 80, 3967-3969.	1.5	1,380
154	Band structure of highly mismatched semiconductor alloys: Coherent potential approximation. Physical Review B, 2002, 65, .	1.1	74
155	Transport-to-quantum lifetime ratios in AlGa <sub>N</sub> /Ga <sub>N</sub> heterostructures. Applied Physics Letters, 2002, 80, 2508-2510.	1.5	38
156	Acoustic phonon scattering of two-dimensional electrons in Ga <sub>N</sub> /AlGa <sub>N</sub> heterostructures. Applied Physics Letters, 2002, 80, 1228-1230.	1.5	51
157	Band anticrossing in Ga <sub>1-x</sub> N <sub>x</sub> alloys. Physical Review B, 2002, 65, .	1.1	67
158	Effects of the narrow band gap on the properties of InN. Physical Review B, 2002, 66, .	1.1	374
159	Band anticrossing in group II-Ox-VI <sub>1-x</sub> highly mismatched alloys: Cd <sub>1-x</sub> Mn <sub>y</sub> OxTe <sub>1-x</sub> quaternaries synthesized by O ion implantation. Applied Physics Letters, 2002, 80, 1571-1573.	1.5	31
160	Band anticrossing effects in Mg <sub>y</sub> Zn <sub>1-y</sub> Te <sub>1-x</sub> Sex alloys. Applied Physics Letters, 2002, 80, 34-36.	1.5	13
161	Band anticrossing in highly mismatched group II-VI semiconductor alloys. Journal of Electronic Materials, 2002, 31, 754-758.	1.0	7
162	Mutual passivation of electrically active and isovalent impurities. Nature Materials, 2002, 1, 185-189.	13.3	55

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163	Band structure and optical properties of $\text{In}_y\text{Ga}_{1-y}\text{As}_x\text{N}_{1-x}$ alloys. <i>Physical Review B</i> , 2001, 65, .	1.1	63
164	Calculation of the ground state of shallow donors in $\text{GaAs}_{1-x}\text{N}_x$ . <i>Journal of Applied Physics</i> , 2001, 89, 789-791.	1.1	6
165	Effect of band anticrossing on the optical transitions in $\text{GaAs}_{1-x}\text{N}_x/\text{GaAs}$ multiple quantum wells. <i>Physical Review B</i> , 2001, 64, .	1.1	83
166	Intrinsic limitations to the doping of wide-gap semiconductors. <i>Physica B: Condensed Matter</i> , 2001, 302-303, 123-134.	1.3	314
167	Effects of structural defects on the activation of sulfur donors in $\text{GaN}_x\text{As}_{1-x}$ formed by N implantation. <i>Physica B: Condensed Matter</i> , 2001, 308-310, 874-876.	1.3	1
168	Band Anticrossing in III-N-V Alloys. <i>Physica Status Solidi (B): Basic Research</i> , 2001, 223, 75-85.	0.7	119
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